

Optically-Coupled Isolator

Optoelectronic Products

MCT2, MCT2E MCT26

General Description

The MCT2, MCT2E and MCT26 optical isolators are electrical and mechanical replacements for the Monsanto series. Optical intercoupling provides a high degree of ac and dc isolation. A capability for continuous operation of the input diode results in a frequency response extending to dc. Connection to the base is also provided for design flexibility.

Glassolated™

Electrically Equivalent to Monsanto Devices

Pin-for-Pin Equivalent to Monsanto Devices

Availability of Base Pin for Flexible Design

Absolute Maximum Ratings

Maximum Temperature and Humidity

Storage Temperature -55°C to $+150^{\circ}\text{C}$

Operating Temperature -55°C to $+100^{\circ}\text{C}$

Pin Temperature (Soldering, 5 s) 260°C

Total Package Power Dissipation

at $T_A = 25^{\circ}\text{C}$,

LED plus Detector 250 mW

Derate Linearly from 25°C 3.3 mW/ $^{\circ}\text{C}$

Input Diode

V_R Reverse Voltage 3.0 V

I_F Forward Current 60 mA

I_{pk} Peak Forward Current,
1 μs pulse width, 330 pps 3.0 A

P_D Power Dissipation
at $T_A = 25^{\circ}\text{C}$ 200 mW

Derate Linearly from 25°C 2.6 mW/ $^{\circ}\text{C}$

Output Transistor

V_{CE} Collector-to-Emitter
Voltage 30 V

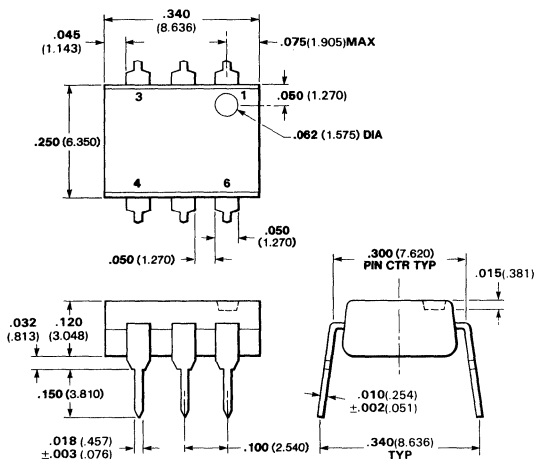
V_{CB} Collector-to-Base Voltage 30 V

V_{EC} Emitter-to-Collector
Voltage 7.0 V

P_D Power Dissipation
at $T_A = 25^{\circ}\text{C}$ 200 mW

Derate Linearly from 25°C 2.6 mW/ $^{\circ}\text{C}$

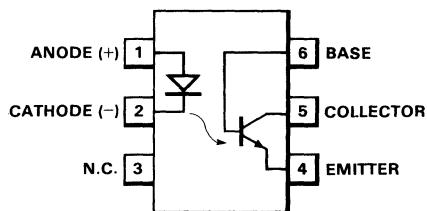
Package Outline



Notes

All dimensions in inches bold and millimeters (parentheses)
 Tolerance unless specified = $\pm .015$ ($\pm .381$)

Connection Diagram DIP (Top View)



Pin

1	Anode (+)	} Input Diode
2	Cathode (-)	
3	NC	
4	Emitter	} Output npn Phototransistor
5	Collector	
6	Base	

Typical Electrical Characteristics

MCT2, MCT2E MCT26

Electrical Characteristics—Input Diode $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
V_F	Forward Voltage		1.25	1.5	V	$I_F = 20\text{ mA}$
BV_R	Reverse Breakdown Voltage	3.0	5.5		V	$I_R = 10\text{ }\mu\text{A}$

Electrical Characteristics—Output Transistor $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
V_{CEO}	Collector-to-Emitter Voltage MCT2/MCT2E	30	65		V	$I_C = 1.0\text{ mA}$, $I_F = 0$
	MCT26	30	75		V	$I_C = 1.0\text{ mA}$, $I_F = 0$
V_{CBO}	Collector-to-Base Voltage MCT2/MCT2E	70	165		V	$I_C = 100\text{ }\mu\text{A}$
	MCT26	30	100		V	$I_C = 100\text{ }\mu\text{A}$
V_{ECO}	Emitter-to-Collector Voltage MCT2/MCT2E	7.0	14		V	$I_C = 100\text{ }\mu\text{A}$
	MCT26	7.0	12		V	$I_C = 100\text{ }\mu\text{A}$
I_{CEO}	Collector-to-Emitter Leakage Current MCT2/MCT2E		5.0	50	nA	$V_{CE} = 10\text{ V}$, $I_F = 0$
	MCT26		5.0	100	nA	$V_{CE} = 5.0\text{ V}$, $I_F = 0$
I_{CBO}	Collector-to-Base Leakage Current MCT2/MCT2E		0.1	20	nA	$V_{CB} = 10\text{ V}$, $I_F = 0$
	MCT26		1.0	100	nA	$V_{CB} = 5.0\text{ V}$, $I_F = 0$
h_{FE}	Forward Current Gain MCT2/MCT2E	100	250			$V_{CE} = 5.0\text{ V}$, $I_C = 100\text{ }\mu\text{A}$
	MCT26	100	150			$V_{CE} = 5.0\text{ V}$, $I_C = 100\text{ }\mu\text{A}$
C_{ce}	Collector-to-Emitter Capacitance MCT2/MCT2E, MCT26		8.0		pF	$V_{CE} = 0$
C_{cb}	Collector-to-Base Capacitance MCT2/MCT2E		20		pF	$V_{CB} = 10\text{ V}$
C_{eb}	Emitter-to-Base Capacitance MCT2/MCT2E		10		pF	$V_{BE} = 0$

Typical Electrical Characteristics (Cont'd)

MCT2, MCT2E MCT26

Electrical Characteristics—Coupled $T_A = 25^\circ\text{C}$

Symbol	Characteristic	Min	Typ	Max	Units	Test Conditions
V_{IO}	Input-to-Output Voltage MCT2 MCT2E MCT26 MCT2, MCT26	1500 2500 1500 800	2300 2500		V_{dc} V_{dc} V_{dc} V_{rms}	$f = 60\text{ Hz}$
$V_{CE(sat)}$	Collector-to-Emitter Saturation Voltage MCT2, MCT2E MCT26		0.24 0.2	0.4 0.3	V V	$I_C = 2.0\text{ mA}$, $I_F = 16\text{ mA}$ $I_C = 250\text{ }\mu\text{A}$, $I_F = 20\text{ mA}$
$I_C/I_F(\text{CTR})$	Collector Current Transfer Ratio (Note 1) MCT2, MCT2E MCT26	20 6	50 14		% %	$V_{CE} = 10\text{ V}$, $I_F = 10\text{ mA}$
R_{IO}	Input-to-Output Resistance MCT2 MCT2E		10^{11} 10^{11}	10^{12}	Ω Ω	$V_{IO} = 500\text{ V}$
C_{IO}	Input-to-Output Capacitance MCT2, MCT2E MCT26		1.0 1.0	2.0	pF pF	$f = 1.0\text{ MHz}$
t_r, t_f	Collector Rise and Fall Times (Note 2) MCT26		2.0		μs	$I_C = 2.0\text{ mA}$, $V_{CE} = 10\text{ V}$

Notes

- Collector current transfer ratio is defined as the ratio of the collector current to the forward bias input current.
- Rise time is defined as the time for the collector current to rise from 10% to 90% of peak value. Fall time is defined as the time required for the current to decrease from 90% to 10% of peak value.